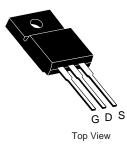


# P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	$R_{DS(on)}$ (Ω) $I_D$ (A) <sup>a</sup> $Q_g$ (1		
- 60	0.0078 at V <sub>GS</sub> = - 10 V	- 98	141 nC	
	0.0098 at V <sub>GS</sub> = - 4.5 V	- 80	141110	

#### TO-220 FULLPAK

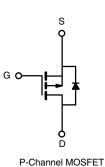


#### FEATURES

- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested

#### **APPLICATIONS**

Load Switch



Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 60	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C		- 98 <sup>a</sup>	
	T <sub>C</sub> = 70 °C		- 56	
	T <sub>A</sub> = 25 °C	I <sub>D</sub>	12 <sup>b</sup>	A
	T <sub>A</sub> = 70 °C		- 8.9 <sup>b</sup>	
Pulsed Drain Current		I <sub>DM</sub>	- 320	
Avalanche Current Pulse	L = 0.1 mH	I <sub>AS</sub>	- 90	
Single Pulse Avalanche Energy	L = 0.1 mm	E <sub>AS</sub>	320	mJ
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	L.	98 <sup>a</sup>	٨
	T <sub>A</sub> = 25 °C	I <sub>S</sub>	3.4 <sup>b</sup>	- A
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		185 <sup>a</sup>	
	T <sub>C</sub> = 70 °C	Б	116 <sup>a</sup>	w
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	4.5 <sup>b</sup>	VV
	T <sub>A</sub> = 70 °C		2.3 <sup>b</sup>	
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b</sup>	Steady State	R <sub>thJA</sub>	35	65	°C/W	
Maximum Junction-to-Case	Steady State	R <sub>thJC</sub>	0.35	0.62	C/W	

Notes:

a. Based on T<sub>C</sub> = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	• Jiii Jei			.,,,,		•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 60			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	1 050		38		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = - 250 μΑ		- 5.2			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1		- 3	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	Inco	$V_{DS} = -48 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1	μΑ	
	IDSS	$V_{DS}$ = - 48 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C			- 10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 98			А	
Drain-Source On-State Resistance <sup>a</sup>	P	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -30 \text{ A}$		0.0078	0.0096	Ω	
	R <sub>DS(on)</sub>	$V_{GS}$ = - 4.5 V, I <sub>D</sub> = - 20 A		0.0098	0.0126		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -50 \text{ A}$		20		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			8500		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = - 48 V, $V_{GS}$ = 0 V, f = 1 MHz		490			
Reverse Transfer Capacitance	C <sub>rss</sub>			280			
Total Gate Charge	Qg	$V_{DS} = -48$ V, $V_{GS} = -10$ V, $I_{D} = -30$ A		141		nC	
	Ũ			39			
Gate-Source Charge	Q <sub>gs</sub>	$V_{\rm DS}$ = - 48 V, $V_{\rm GS}$ = - 4.5 V, $I_{\rm D}$ = - 20 A		16			
Gate-Drain Charge	Q <sub>gd</sub>			23			
Gate Resistance	Rg	f = 1 MHz		4.5		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			70			
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 48 V, $R_L$ = 2 $\Omega$		155		- ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_{D}\cong$ - 10 A, $V_{GEN}$ = - 10 V, $R_{g}$ = 1 $\Omega$		210			
Fall Time	t <sub>f</sub>			160			
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	ا <sub>S</sub>	$T_{C} = 25 \ ^{\circ}C$			- 98	A	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 320		
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 30 A		- 0.7	- 1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			48		ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = - 50 A, di/dt = 100 A/μs, T <sub>.I</sub> = 25 °C		59		nC	
Reverse Recovery Fall Time	t <sub>a</sub>	$r_F = -50$ A, $u/ut = 100$ A/ $\mu$ s, $r_J = 25$ °C		29			
Reverse Recovery Rise Time				12		ns	

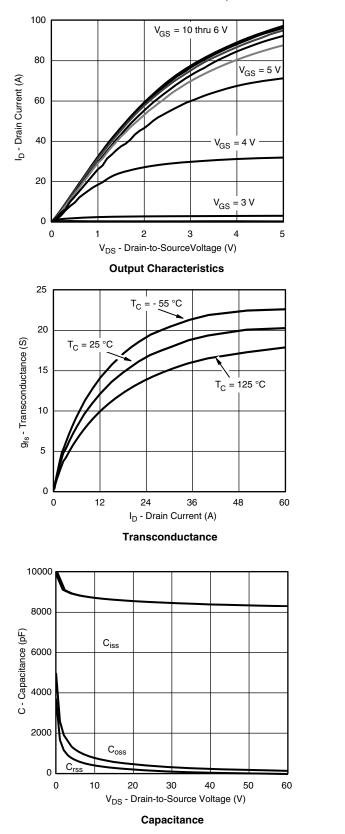
Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

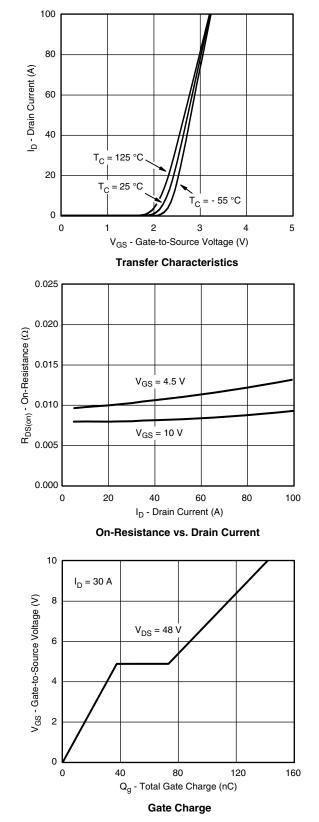
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



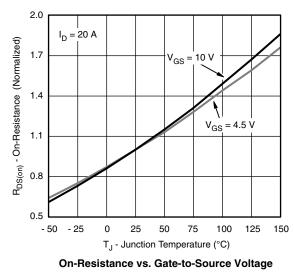


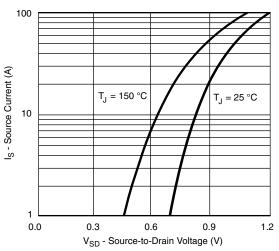
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



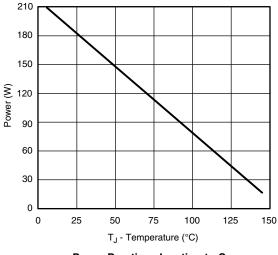


### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

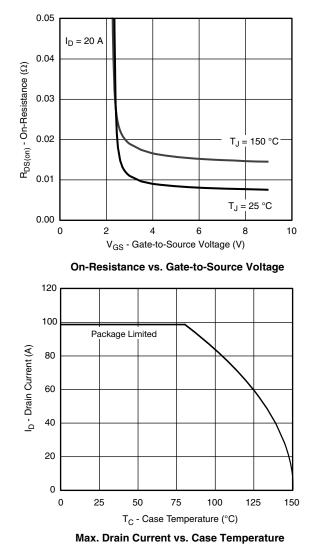


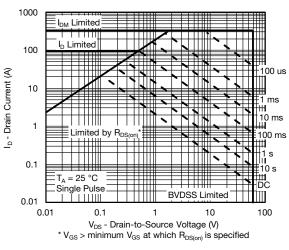


Source-Drain Diode Forward Voltage



Power Derating, Junction-to-Case

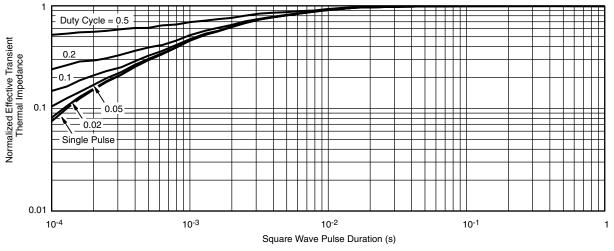




Safe Operating Area, Junction-to-Ambient



#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



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